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DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING
EXAMINATIONS 2007

MSc and EEE PART III/IV: MEng, BEng and ACGI

ANALOGUE INTEGRATED CIRCUITS AND SYSTEMS

Wednesday, 2 May 10:00 am

Time allowed: 3:00 hours

There are SIX questions on this paper.

Answer FOUR questions.

All questions carry equal marks

Any special instructions for invigilators and information for candidates are on page 1.

Examiners responsible First Marker(s) : C. Toumazou
 Second Marker(s) : D.G. Haigh

1. (a) The circuit shown in Figure 1.1 is a single-stage inverting voltage amplifier using two CMOS FETs. Write a simple SPICE programme which will compute a small signal gain and phase frequency response analysis of the circuit over the frequency range 10 kHz to 10 MHz. The .OPTIONS card and the transistor model process parameters QP and QN are already built into the SPICE Library.

[6]

- (b) Sketch and label typical phase and gain characteristics of the amplifier. What effect does cascoding have on amplifier performance in particular amplifier phase margin.

[6]

- (c) What is the function of the passive components C_1 , R_1 and R_2 shown on the circuit?

[4]

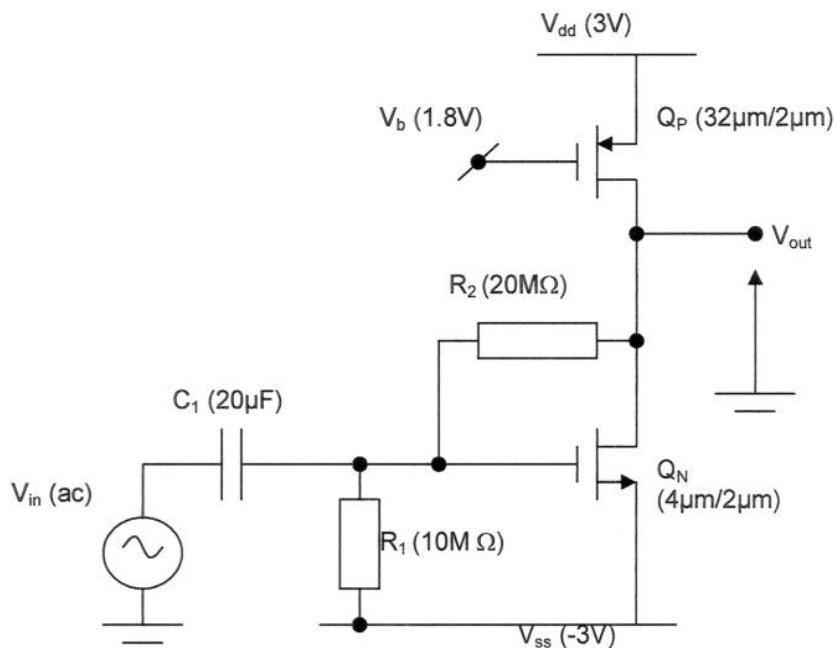


Figure 1.1

- d) In practice voltage reference V_b is provided by an on-chip voltage reference circuit similar to the one shown in Figure 1.2. Explain qualitatively why such a four transistor reference circuit can have smaller chip area than an equivalent two transistor circuit with the same power consumption

[4]

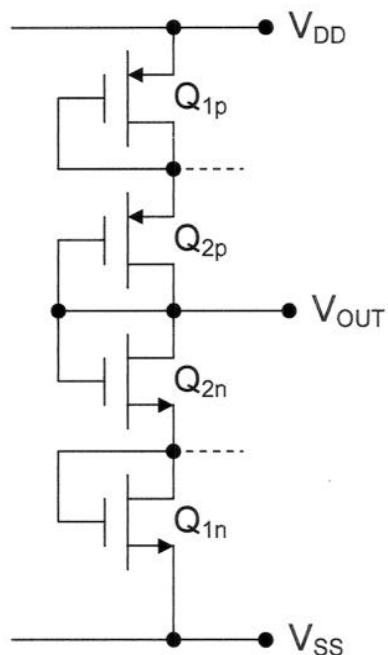


Figure 1.2

2. (a) Voltage and current-sources are key components in analogue circuit design. Sketch a typical band-gap voltage reference circuit and prove that the temperature coefficient of the output voltage V_o is zero if $V_o = 1.283$ V. Assume the temperature coefficient of V_{BE} to be $-2.5\text{mV}^{\circ}\text{C}$, Boltzmann's constant $k = 1.38 \times 10^{-23} \text{ J/K}$ and electron charge $q = 1.6 \times 10^{-19} \text{ C}$.

[11]

- (b) Calculate the fractional temperature coefficient for the constant current generator of Figure 2 at room temperature, given that R is a polysilicon resistor with a temperature coefficient of 1500 ppm/ $^{\circ}\text{C}$. What is the function of the four diodes ?

[5]

- (c) Explain why transistor Q_2 in figure 2 has two emitters and also why the output current I_o is directly proportional to absolute temperature.

[4]

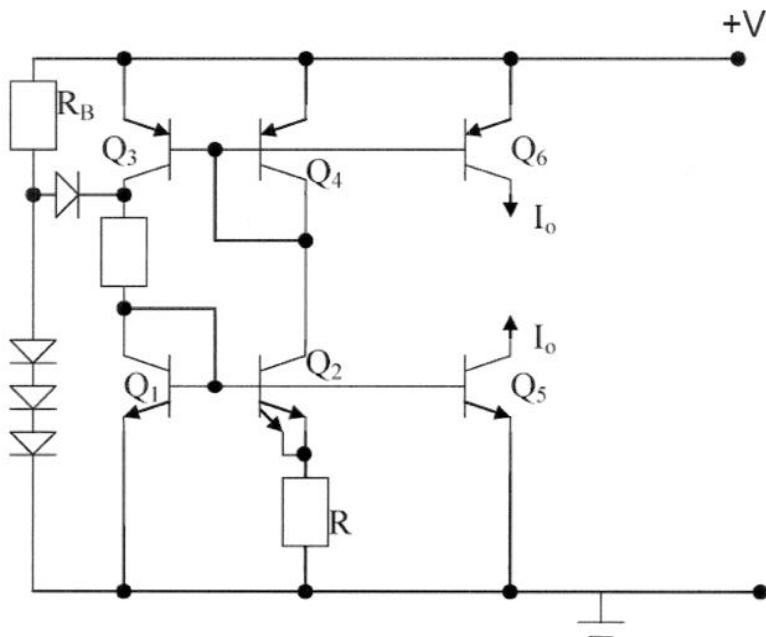


Figure 2

3. (a) Sketch a typical circuit diagram for a single-stage fully differential folded cascode CMOS op-amp. Why is the folded cascode op-amp regarded as a single stage design? Finally briefly explain the concept of common-mode feedback with reference to your folded cascode op-amp.

[8]

- (b) Estimate the low-frequency differential voltage gain, slew rate and gain-bandwidth product of the two-stage CMOS op-amp shown in Figure 3.1. Aspect ratios of all devices are shown on the circuit. Assume all bulk effects are negligible. Device model parameters are given below.

[10]

- (c) Explain qualitatively why the addition of a resistor in series with compensation capacitor C_c improves amplifier stability.

[2]

CMOS TRANSISTOR PARAMETERS

MODEL PARAMETERS	$K_p (\mu A/V^2)$	$\lambda (V^{-1})$	$V_{TO} (V)$
PMOS	20	0.03	-0.8
NMOS	30	0.02	1.0

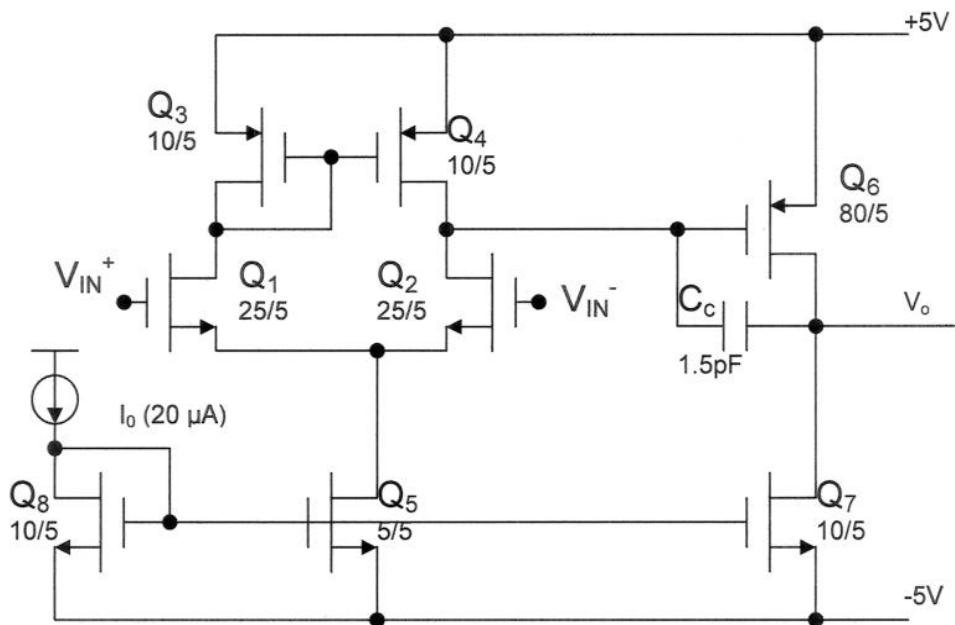


Figure 3.1

4. (a) Under what operating conditions does the MOSFET of Figure 4.1 realise a linear floating resistor between terminals A and B? Show that under these conditions the equivalent resistance R_{AB} can be approximated by

$$R_{AB} = \frac{L}{KW(V_{GS} - V_T)}$$

stating any assumptions. All symbols have their usual meaning.

[6]

- (b) Discuss three sources of non-linearity in the single MOSFET resistor realisation of Figure 4.1 and suggest one suitable circuit design to help eliminate one or more of these non-linear terms. Show all necessary circuit analysis to confirm your design.

[6]

- (c) Figure 4.2 shows a fully differential continuous time integrator using a balanced double differential linear active transresistor. Derive an expression for the time constant of the integrator. You may ignore all bulk effects, and assume all MOSFETs are operating in the triode region.

[8]

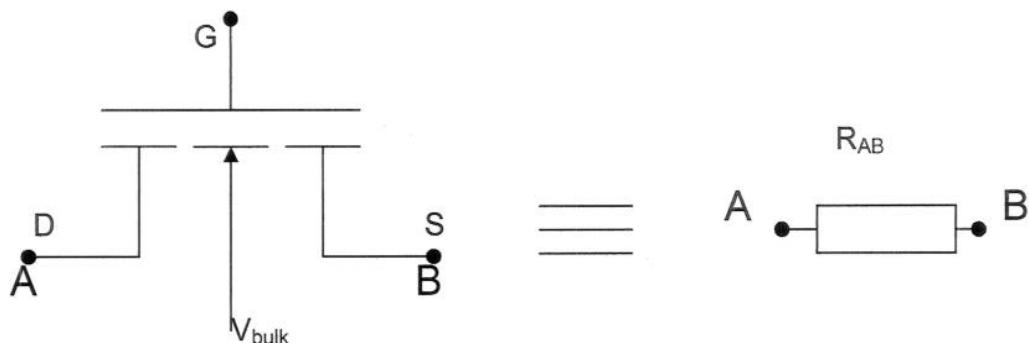


Figure 4.1

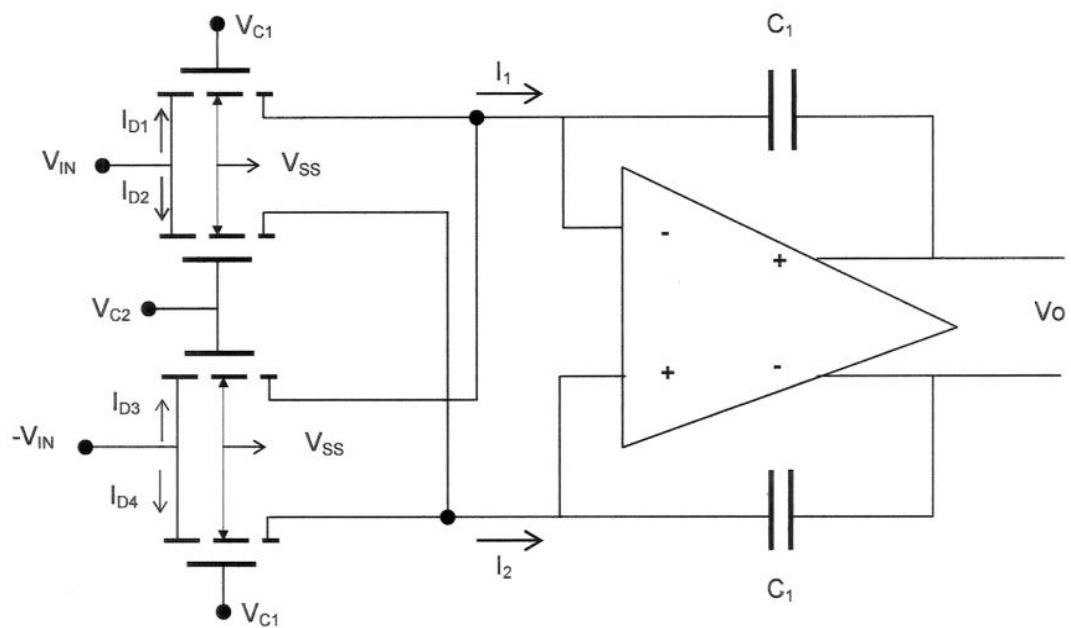


Figure 4.2

5. (a) Sketch circuits for both a Lossy and differential switched-capacitor integrator and derive an expression for the transfer function of each implementing switches by MOSFETs of equal size and assuming that the integrators are driven by non-overlapping clocks with a clock frequency much higher than the maximum input signal frequency. Also assume the switches are ideal.

[10]

- (b) Figure 5.1 shows one section of a switched capacitor ladder filter. Based on this filter structure, design a 3rd-order Chebyshev low-pass filter with a cut-off frequency of 5 kHz and a 1.0 dB pass band ripple. Assume a clock frequency of 100 kHz. Passive component values for the LC prototype, normalised to 1 rad/s, are $C_1 = C_3 = 2.0236$, $L_2 = 0.994$. In your analysis assume all integrators to be lossless.

[10]

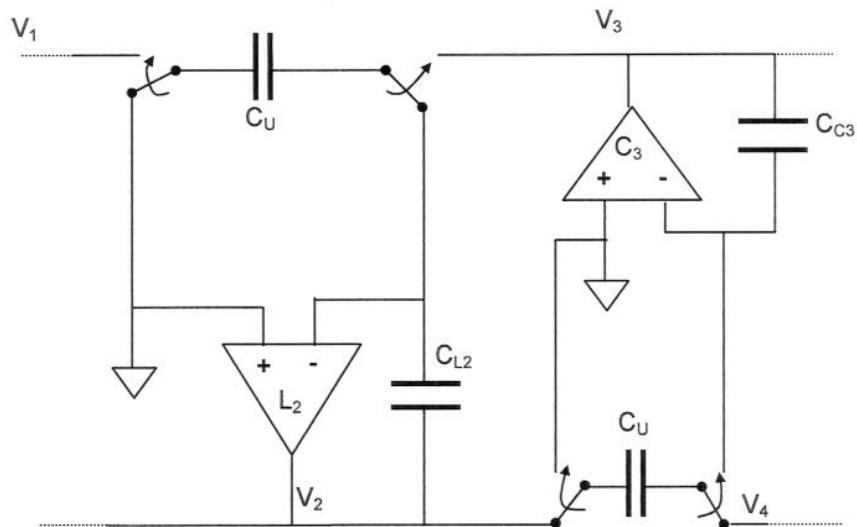


Figure 5.1

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6. (a) Give one advantage and one disadvantage of each of the three CMOS current mirror circuits shown in Figures 6.1, 6.2 and 6.3. [6]
- (b) For the current mirror of Figure 6.2 derive the voltage swing in terms of device threshold voltage V_T , clearly stating any assumptions you make. [7]
- (c) With the aid of a macromodel, explain the theoretical concept of current feedback and how it results in constant bandwidth application. [7]

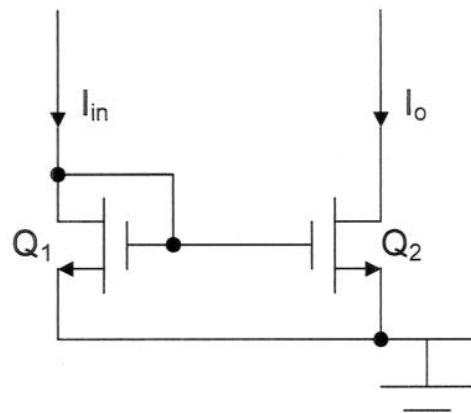


Figure 6.1

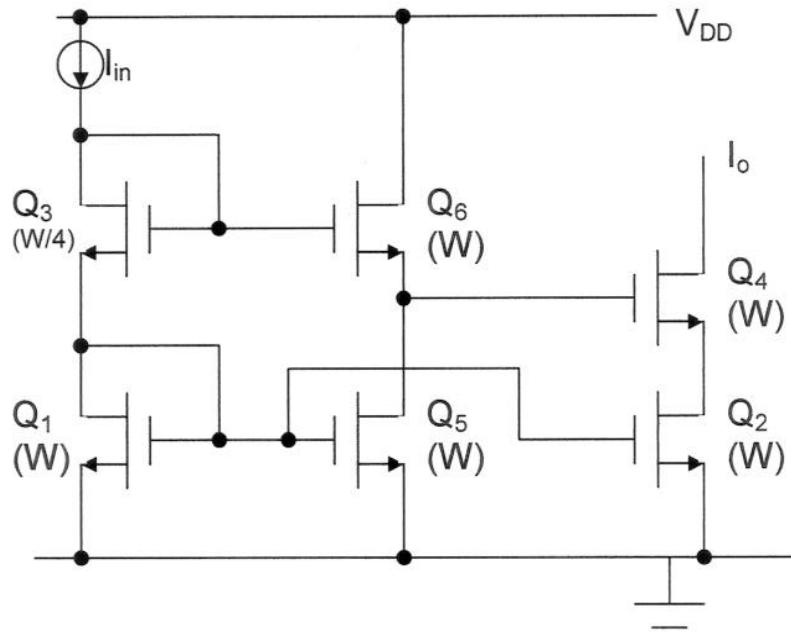


Figure 6.2

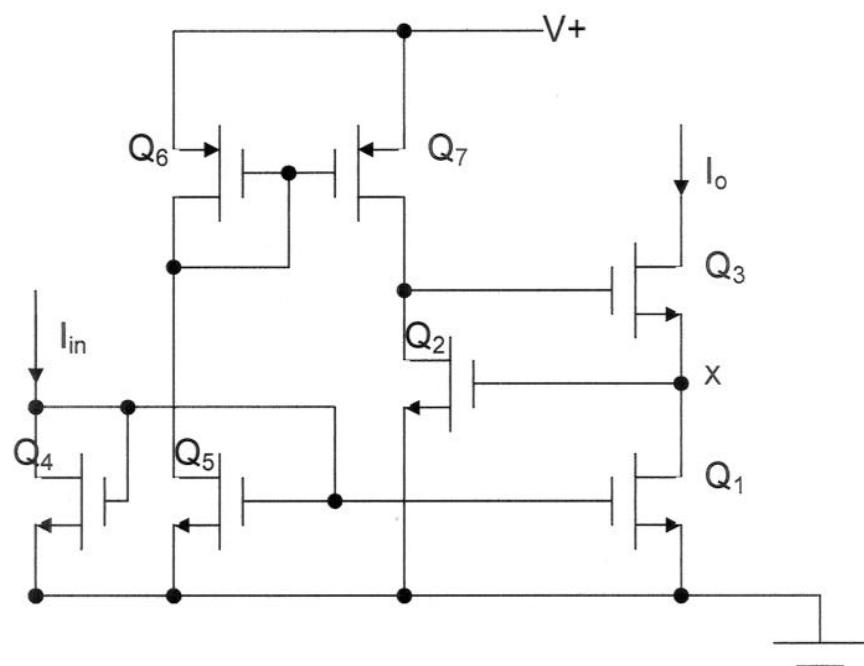


Figure 6.3

E3.01 / ACI

2007 Exam. organized.

3rd Year / Msc

Analogue Integrated Circuits
and Systems

E3.01 / ACI

SOLUTIONS

1st Marker

C. Toumazou

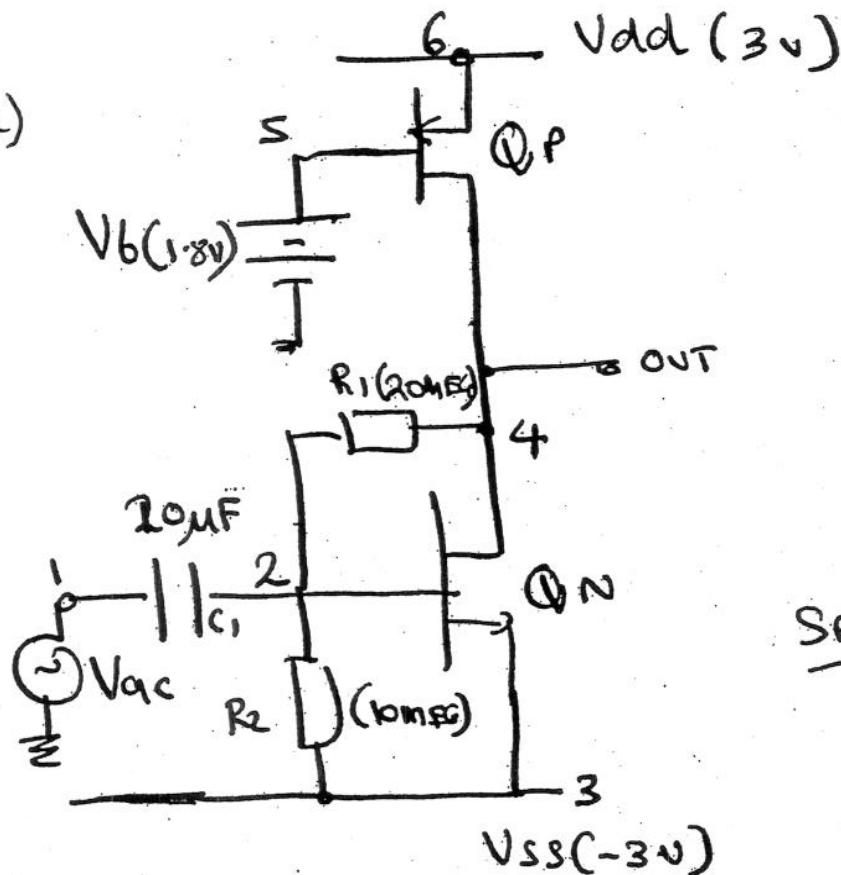
and Marker

D. H. Quigley

Q1

21
1

a)



- Title inverting cmos amplifier.

Component Netlist	C1	1	2	20 E-6	
	R1	2	4	20 MEG	
	R2	2	3	10 MEG	
	M1	4	2	3	QN W=4u L=2u
	M2	4	5	6	QP W=32u L=2u
	Vdd	6	0	3V	
	Vss	3	0	-3V	
	Vb	5	0	1.8V	
Vac	1	0	ac	1	sources

- model QN, QP

- op all

- option post

- AC dec 10% 10K 10MEG

- PRINT ac Vd(B(4))

- PRINT ac VP(4)

- END.

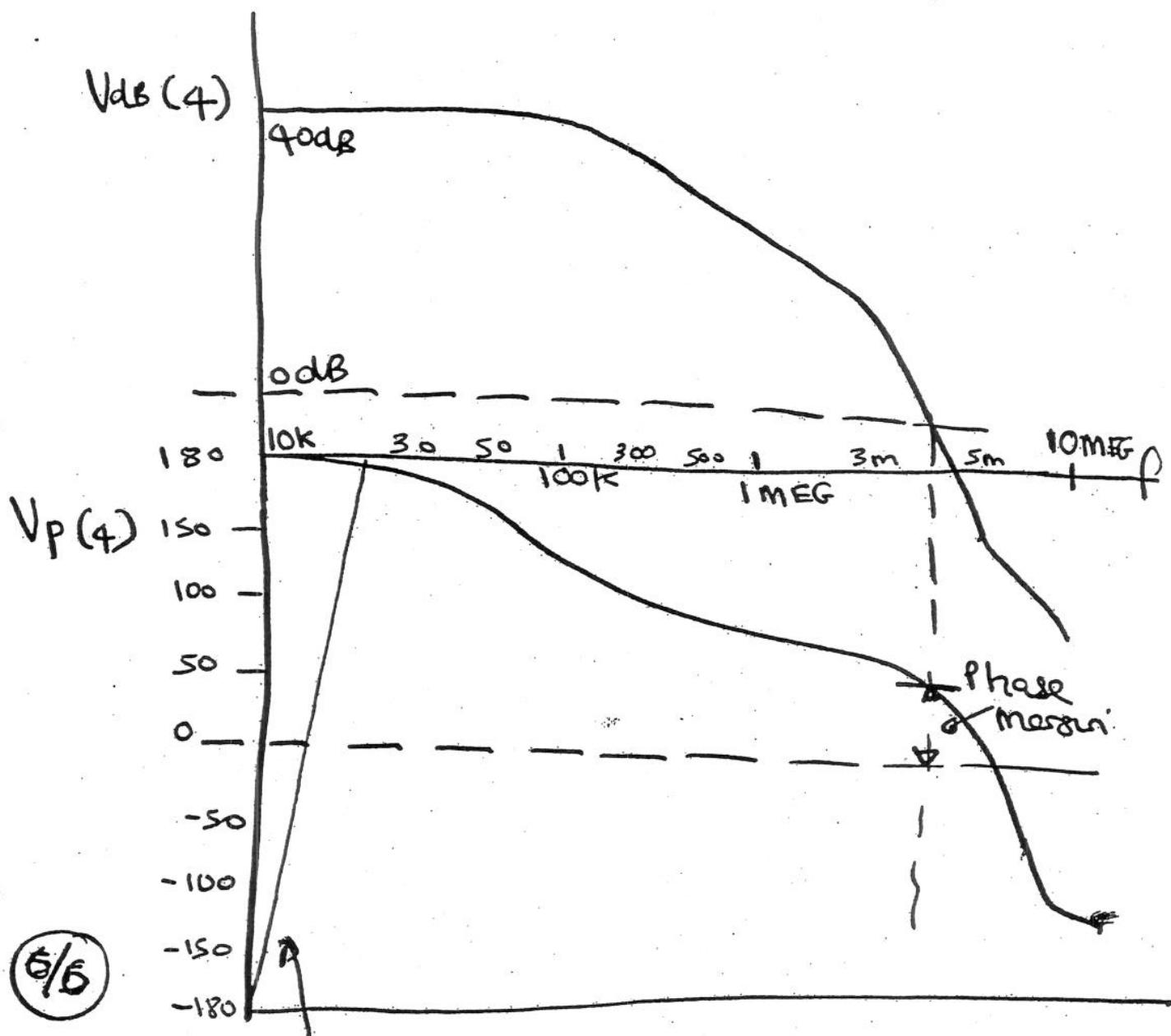
Analysis
Print

CT

Q1 (cont)

Typical SPICE output Plot

(2)



Auto Scaling in SPICE

Likely that theory and simulated will differ because of approximations generally assumed in theory. Models for transistors in SPICE have inaccuracy. Also inaccuracy in parameter extraction for SPICE models.

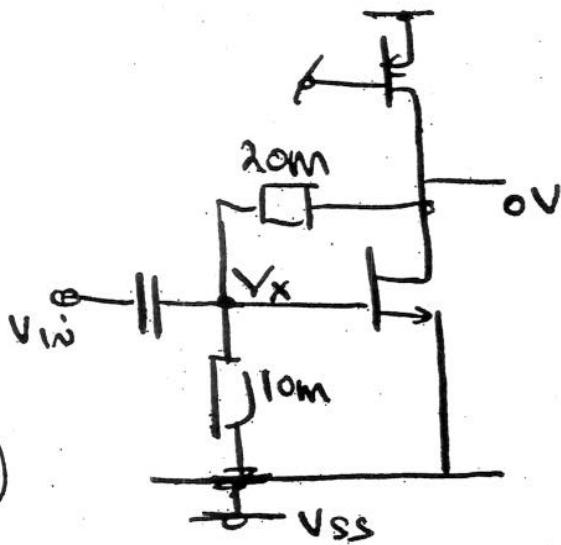
Cascoding will increase amplifier gain but will compromise phase margin due to added capacitance at output.

CT

Q1 (Cont.)

(3)

Large Passive Components need DC biasing.
Sets high impedance output of amplifier at
DC bias close to 0V. Large values of R
used so that input and output impedance
levels are not loaded. $20\mu F$ capacitor
used to ac couple input. Typically



$$V_x = V_{SS} + \left(-\frac{V_{SS}}{3}\right) 2$$
$$= \left[\frac{V_{SS}}{3}\right]$$

4/4

CT

(4)

Figure Q1 d)

Q1 cont

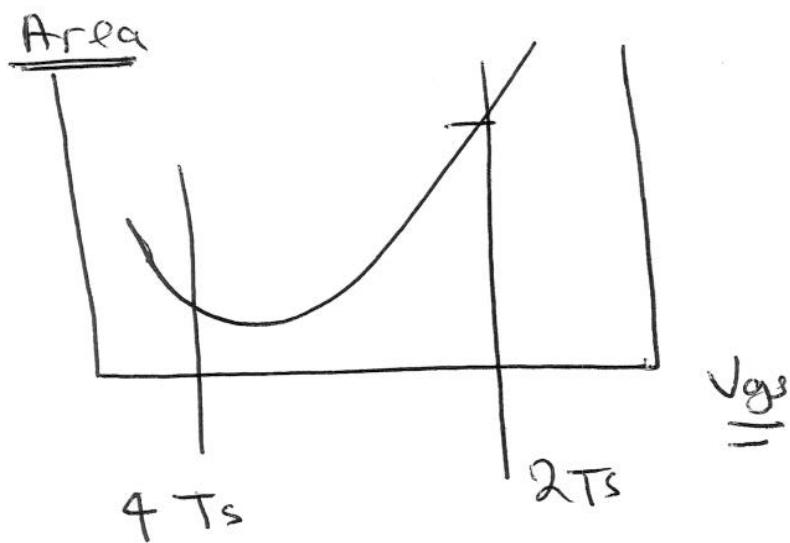
$$\text{Since } I = \frac{k_w}{2L} (V_{GS} - V_T)^2$$

Then if V_{GS} is small $\approx V_T$ then (W/L) large.If $V_{GS} \gg V_T$, then (W/L) smallsmall (W/L) gives large chip area

∴ Two transistors PD has

larger V_{GS} / transistor than

one transistor PD for same supply



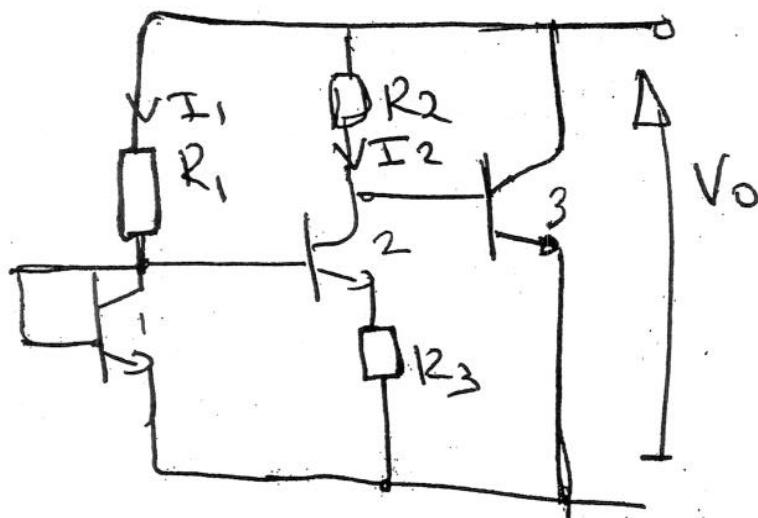
4/4

C7

5

Ans 2

Q2



Bandgap.

(S/S)

$$V_{BIE1} = V_{BE2} + I_2 R_3$$

$$\beta \gg 1$$

$$\text{Since } V_{BIE1} - V_{BE2} = VT \ln\left(\frac{I_1}{I_2}\right)$$

$$\text{Then } V_0 = V_{BE3} + R_2/R_3 VT \ln\left(\frac{I_1}{I_2}\right)$$

\uparrow
 $VT \ln\left(\frac{I_3/I_s}{I_s}\right) \rightarrow \text{assume}$

for $dV_0/dt = 0$, then dV_{BE3}/dT

$$= \frac{V_T}{T} \frac{R_2}{R_3} \ln\left(\frac{I_1}{I_2}\right)$$

$$\text{Since } \frac{dV_{BE}}{dT} \approx -2.5 \text{ mV/}^\circ\text{C}, \quad \frac{V_T}{T} = \frac{1.38 \times 10^{-23}}{1.6 \times 10^{14}}$$

$$\text{Then } \left(\frac{R_2}{R_3}\right) \ln\left(\frac{I_1}{I_2}\right) = 29 \text{ and so}$$

6/6

$$V_0 = 1.283 \text{ V}$$

b) For PTAT

Temperature coefficient of V_T cancels with negative temp coefficient of Resistor

C+

Qn 2 cont

(6)

$$TCF = \frac{1}{VT} \partial VT / \partial T - \gamma_R \partial R / \partial T$$

$$= \frac{1}{T} - 1500 \times 10^{-6} \ell_{\text{Room}} T$$

$$= 1833 \text{ ppm/}^{\circ}\text{C}$$

(3/3)

The diodes are part of a start-up circuit which will conduct when the P-TAT is in its 'zero' operating state. An injection of current is provided by R_B which starts-up the circuit switching off the diode connected to the collector of Q_3 .

TOTAL

20/20

(2/2)

(4/4)

c). since $I_0 = \frac{(V_{be1} - V_{be2})}{R}$

Prop to
temperature

$$= \frac{VT}{R} \ln \left[\frac{I_1}{I_0} \frac{I_{S2}}{I_{S1}} \right] \approx \frac{VT \ln 2}{R}$$

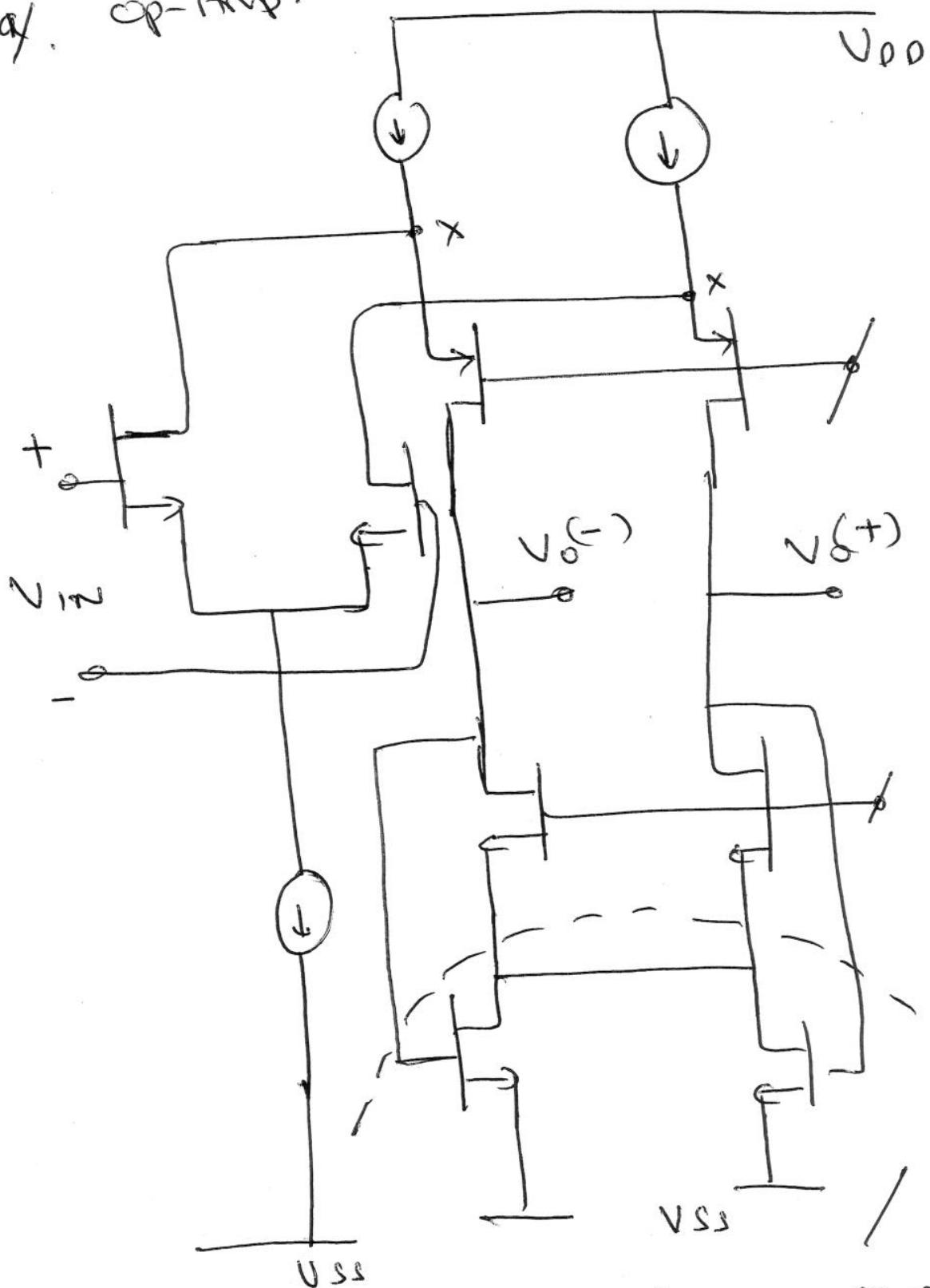
If $I_{S2} = I_S$, and $I_0 = I_1$, then $I_0 \approx 0$. $I_{S2}/I_{S1} = n = 2$ in this case.

(7)

Qu 3

Architecture of folded-cascode

a. op-Amp.



(4)

$$A \approx (\gamma_2) \left(\frac{8m}{g_o}\right)^2$$

common-mode
feedback.

(T)

(8)

Qn 3 cont

Single-stage because one current path from input to output.

Node X is low impedance and so very small voltage swing is generated. Only high impedance

node is at the output.

(2)
Not necessary to pole split since dominant pole at output not two stages.

Diff output op-amp with high gain have no way of stabilization since outputs are undriven (voltage limit is).

(common-mode feedback - senses common-mode output and via negative feedback controls the current through the output stage to ensure stable quiescent operating point. Circuit shown in the figure.)

(2)

b). OP-Amp

(2/2) $A_{v1} = -gm_2 / (g_{o2} + g_{o4})$

$$(g_{o2} + g_{o4}) = I_{D2} (\lambda_N + \lambda_P)$$

$$= 5 \times 10^{-6} \times 0.05 = 2.5 \times 10^{-7} \text{ A}^{-1}$$

$$gm_2 = 2 \sqrt{\beta_2 I_D} \Rightarrow \beta_2 = \frac{k_N}{2} \left(\frac{W}{L} \right)_2$$

$$\beta_2 = 7.5 \times 10^5 \text{ A/V}$$

$$\therefore gm_2 = 3.87 \times 10^{-5} \text{ s}$$

(2/2) $A_1 = \underline{-154.9}$

$$A_n = \boxed{-gm_6 / (g_{o7} + g_{o6})}$$

$$(g_{o6} + g_{o7}) = I_{D6} (\lambda_{NP} + \lambda_N)$$

$$= 20 \times 10^{-6} \times 0.05$$

$$= 10 \times 10^{-7} \text{ A}^{-1}$$

(2/1) $gm_6 = 1.13 \times 10^{-4}, A_2 = -113.$

$$AT = A_1 A_2 = 17563$$

Qn 3 cont

(10)

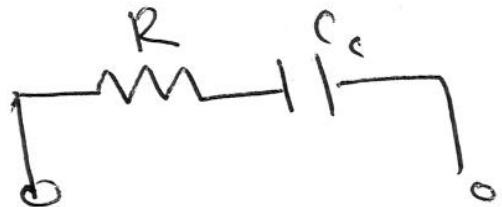
$$G \cdot B_P = \frac{g_m^2}{2\pi C_C} = 4.1 \text{ MHz} \quad -\textcircled{2}$$

$$S \cdot R = I_0 / C_C = \left(\frac{10}{1.5}\right) V/\mu s \quad -\textcircled{2}$$

- TOTAL $10/10$

—————/1—

c. Introduce R in series with C_C X



provides feedforward compensation
and eliminates RHP zero in the
op-amp's transfer function.

Zero is given by $Z = -g_m R / C_C$
with R

$$Z = -\frac{1}{(1/g_m - R) C_C} \cdot \text{Improve } \phi$$

by setting $Z = P_2 = 2nd$ pole.
with R .

(2/2)

(T)

Q4

(11)

a) Assumption is that if ($V_{DS} \approx 0$) or ($V_{DS} \ll V_{GS} - V_T$) device acts in linear region. From

$$I_D = \frac{k_W}{L} [(V_{GS} - V_T)V_{DS} - V_{DS}^2/2] (1 + V_{DS})$$

for $V_{DS} \ll (V_{GS} - V_T)$, then $\rightarrow V_{DS} \ll 1$

$$\text{So } I_D = \frac{k_W}{L} (V_{GS} - V_T)V_{DS}$$

6/6

$$\text{OR } R_{AB} = V_{DS}/I_D = L/(k_W(V_{GS} - V_T))$$

b)

Three sources of non-linearity

(i) limited due to V_{BS} changing V_T

for negative V_{DS} due to body effect.

$$\text{i.e. } V_T = V_{TO} + \gamma [\sqrt{-V_{BS} + 2\phi_F} - \sqrt{2\phi_F}]$$

γ = bulk threshold parameter

ϕ_F = Fermi-level potential

(ii) limited due to V_{DS} approaching $(V_{GS} - V_T)$ hence saturation region

for large positive V_{DS} .

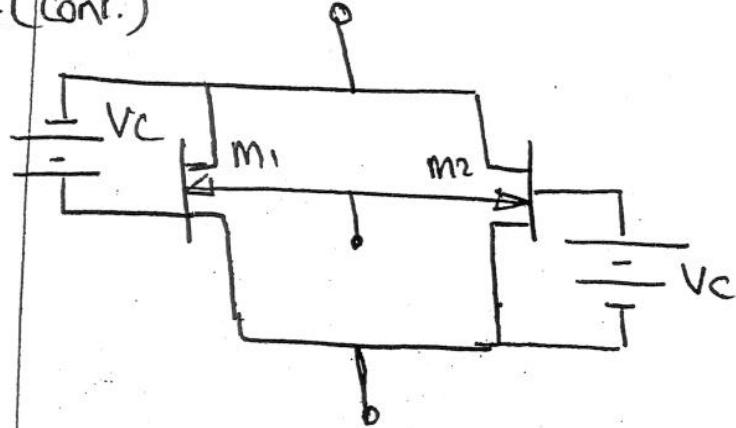
(iii) For large values of V_{DS} the $V_{DS}^2/2$ term comes in making the result quite non-linear.

4/A

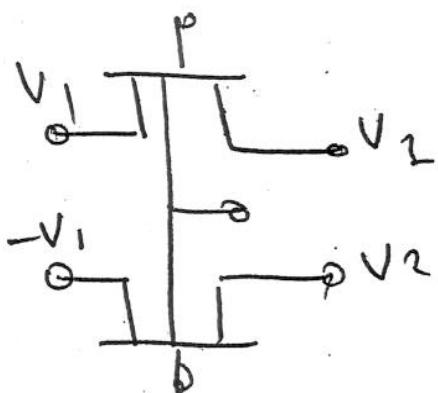
(T)

Q4 (cont.)

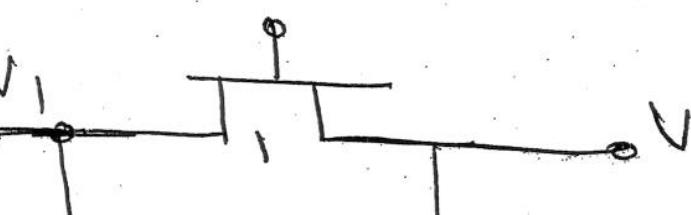
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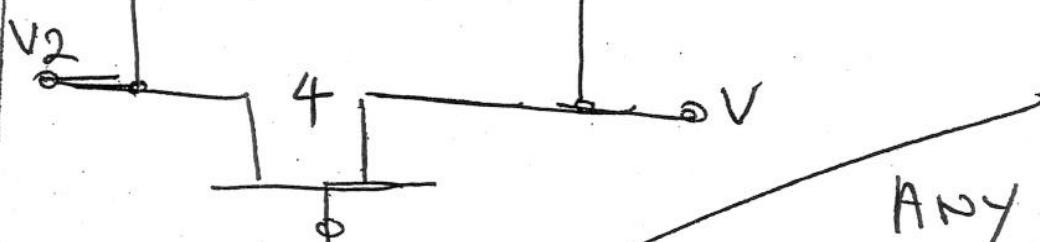
Parallel circuit - eliminates $V_{DS}^2/2$ term.



Differential scheme



Double differential
mos.
Eliminates
- V_{DS} and V_T
term.



Any one
of these
will do!

2/2

(T)

Q4 (cont)

Double differential integrator

(B)

$$I_{D1} = 2\beta [(V_{C1} - V - V_T)(V_1 - V) - \frac{1}{2} (V_1 - V)^2]$$

$$I_{D2} = 2\beta [(V_{C2} - V - V_T)(V_2 - V) - \frac{1}{2} (V_2 - V)^2]$$

$$I_{B3} = 2\beta [(V_{C2} - V - V_T)(V_2 - V) - \frac{1}{2} (V_2 - V)^2]$$

$$I_{D4} = 2\beta [(V_{C1} - V - V_T)(V_2 - V) - \frac{1}{2} (V_2 - V)^2]$$

Expanding it can be shown that :-

$$(V_1 - V_2)(I_1 - I_2) = \frac{1}{2}\beta(V_{C1} - V_{C2}) = R$$

Independent of both V_T and V_{DS} terms

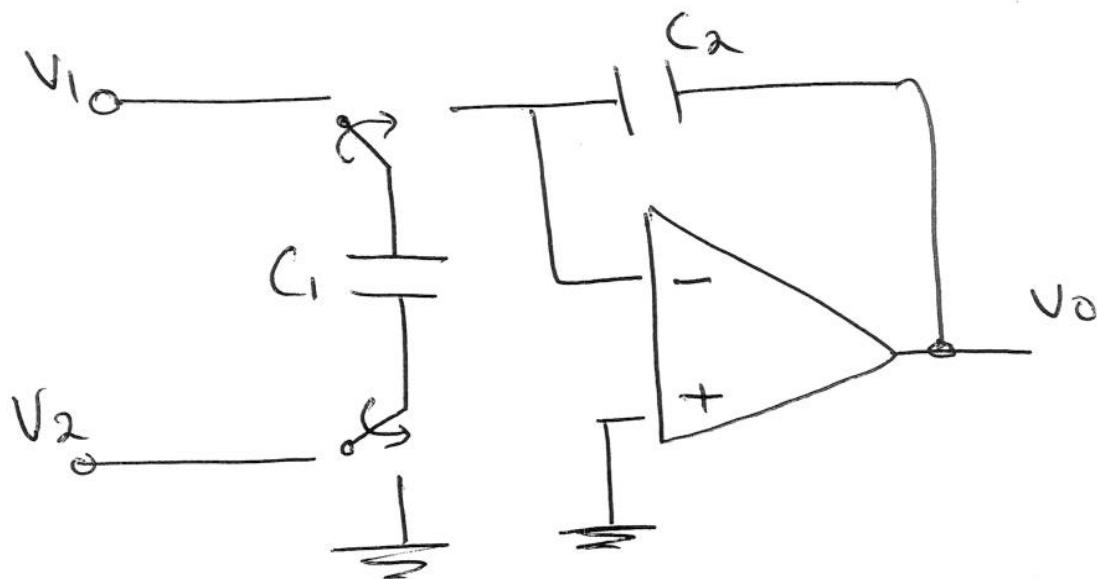
Hence $N = \frac{2CR}{\beta(V_{C1} - V_{C2})}$

8/8

CT

Ques/.

a) Differential Integrator



During ϕ_1 , $Q = C_1 [V_1, -V_2]$

$$I_{av} = f_c C_1 [V_1, -V_2]$$

f_c = clock frequency

During $\phi_2 \Rightarrow I_{av} = -f_c (V_1 - V_2) C_1$

$$\therefore V_0 = \frac{-1}{j\omega C_2} f_c C_1 [V_1, -V_2]$$

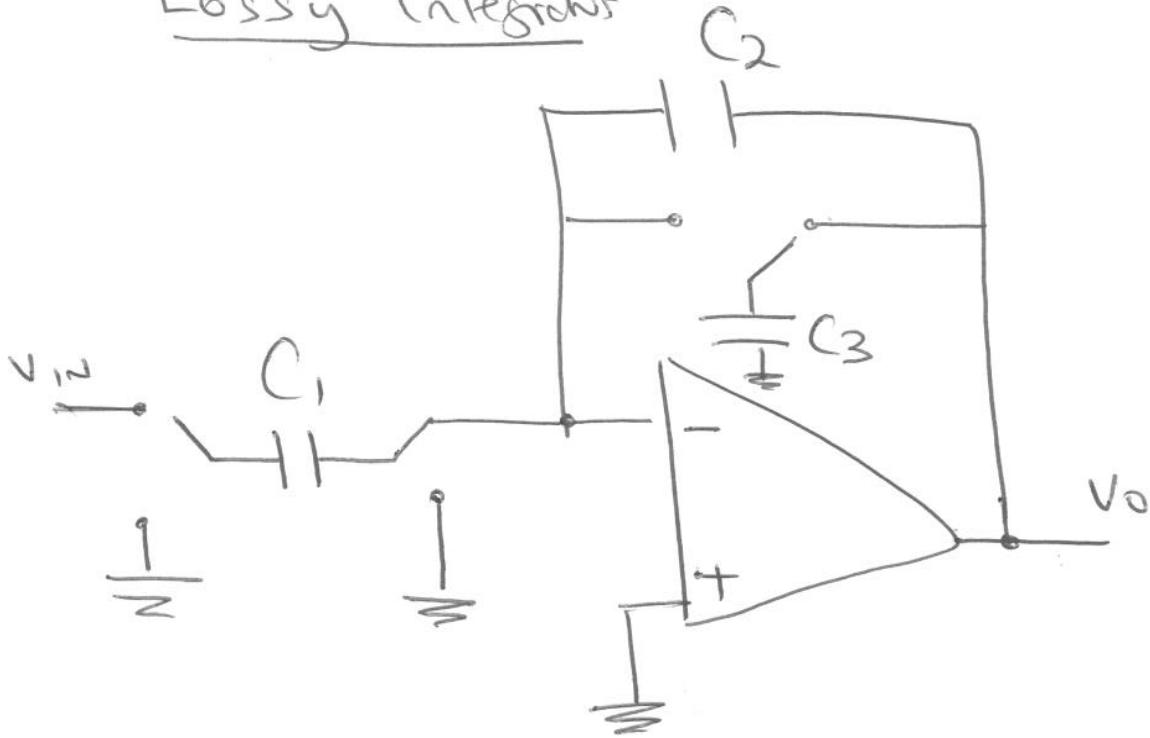
$$\therefore \frac{V_0}{(V_1 - V_2)} = -\frac{f_c}{j\omega C_2} \frac{C_1}{C_2} \approx T = \frac{C_2}{C_1} f_c$$

(5/5)

Aus cont

(15)

Lossy Integrators



Durch ϕ_1 $\phi = C_1 V_{IN} \Rightarrow I_{AV} = f_c C_1 V_{IN}$

Durch ϕ_2

$$I_{AV} = - \left[f_c (C_3 V_0 + j\omega C_2 V_0) \right]$$

$$\therefore f_c C_1 V_{IN} = - \left[f_c (C_3 V_0 + j\omega C_2 V_0) \right]$$

$$V_{IN} = - \left[\frac{C_3}{C_1} V_0 + \frac{j\omega C_2 V_0}{C_1 f_c} \right]$$

∴ $\frac{V_0}{V_{IN}} = - \frac{C_1}{C_3} \left(\frac{1}{C_1 + \frac{C_2 j\omega}{C_3 f_c}} \right)$

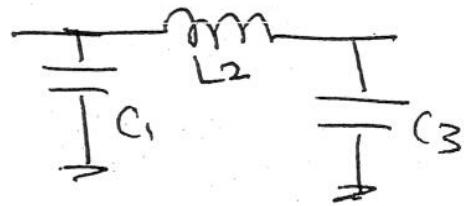
$\approx T = \left(\frac{C_2}{C_3} \right) \frac{1}{f_c}$

5/5

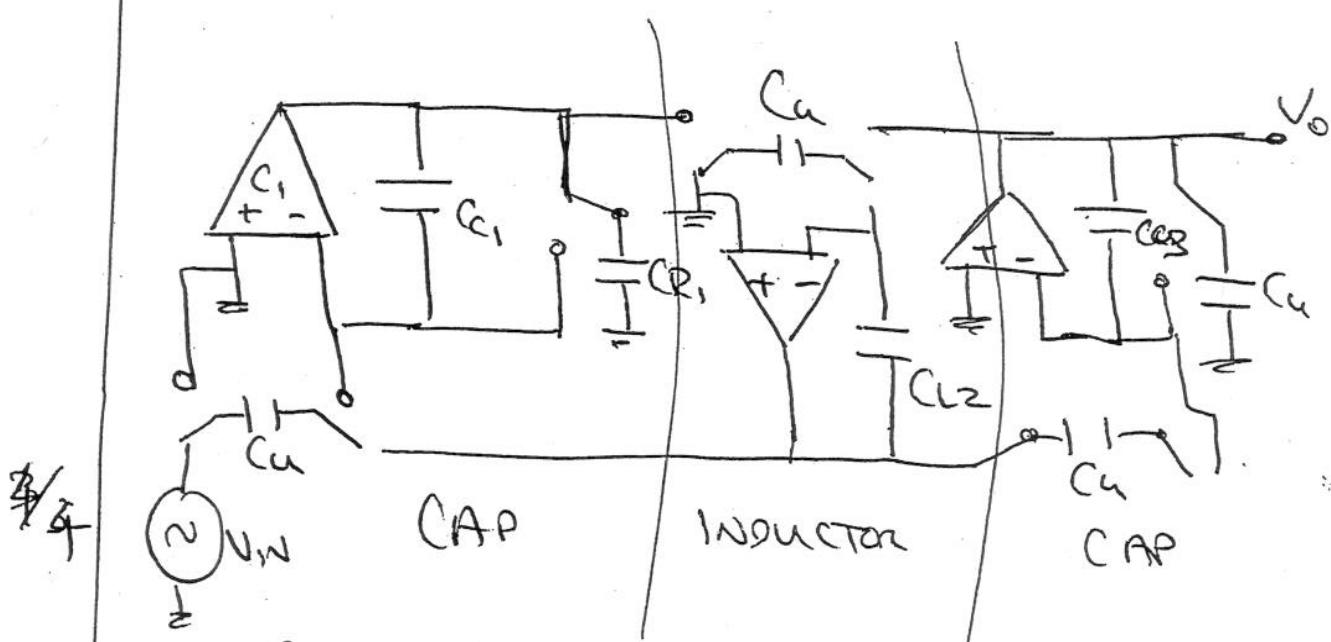
Ques 5 (cont)

Section of LCR prototype.

(16)



General transformation Rules (not really required but the bright students may include)



Conversions to differential equations,

Inductor transformer

$$(L_2/R_S) f_c = C_{12}/C_u$$

Capacitor Transformer.

$$(C_3/C_u = f_c R_S C_3)$$

where R_S is non-existing dummy scaling factor. Assuming $R_S = 1$,

$$C_1/C_u = f_c C_1$$

$$C_3/C_u = f_c C_3$$

$$C_{12}/C_u = f_c L_2$$

} general transformer

(T)

Ans cont

(17)

Table values of C_1 , L_2 and C_3
are normalized to 1 rad/s $\div 2\pi f_p$

$$f_p = 5 \text{ kHz}$$

$$C_1 = C_3 = 2.0236 / (2\pi 5 \times 10^3) \\ = 6.44 \times 10^{-5} \text{ F}$$

$$C_{L2} = 0.994 / (2\pi 5 \times 10^3) \\ = 3.164 \times 10^{-5} \text{ F}$$

For terminated R_s

assume $C_{in} = C_{R1} = C_{Ro} = 1 \text{ pF}$

Then
$$\begin{cases} C_{L1} = C_{e3} = 6.44 \text{ pF} \\ C_{L2} = 3.164 \text{ pF} \end{cases}$$

6/6

To M 20/20

(T)

Ques 6/.

a)

Fig 6.1 - Single末级

- Advantages -
- High frequency
- High output swing

② Disadvantage - very inaccurate

Fig 6.2 - High swing cascade

- Advantage - High output swing
- than cascode

② Disadvantage - complex, poor frequency performance.

Figure 6.3 - Regulated cascade

- Advantage -
- highest output swing
- lowest output resistance

Disadvantage -

- inaccuracy of input current-mirror
- feedback leading to potential instability.

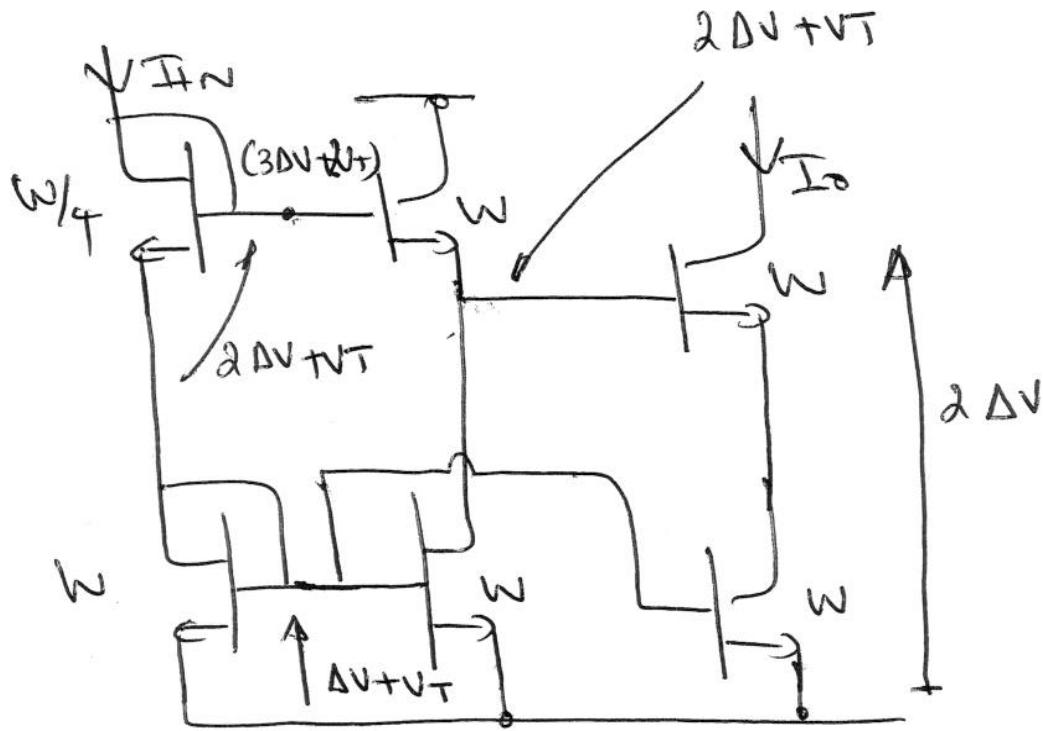
6/6

Qn 6 cont

(19)

output swing

Circuit includes all saturation Voltages



Assuming equal L's

$$I_0 = I_{IN}$$

$$\beta_1 = \beta_2 = \beta_4 \quad \beta_5 = \beta_6 = \beta$$

$$\beta_3 = \beta/4$$

(7/7)

$$\therefore V_{sat} = 2(V_{GS} - V_T)$$

NOTE $\Delta V = (V_{GS} - V_T)$

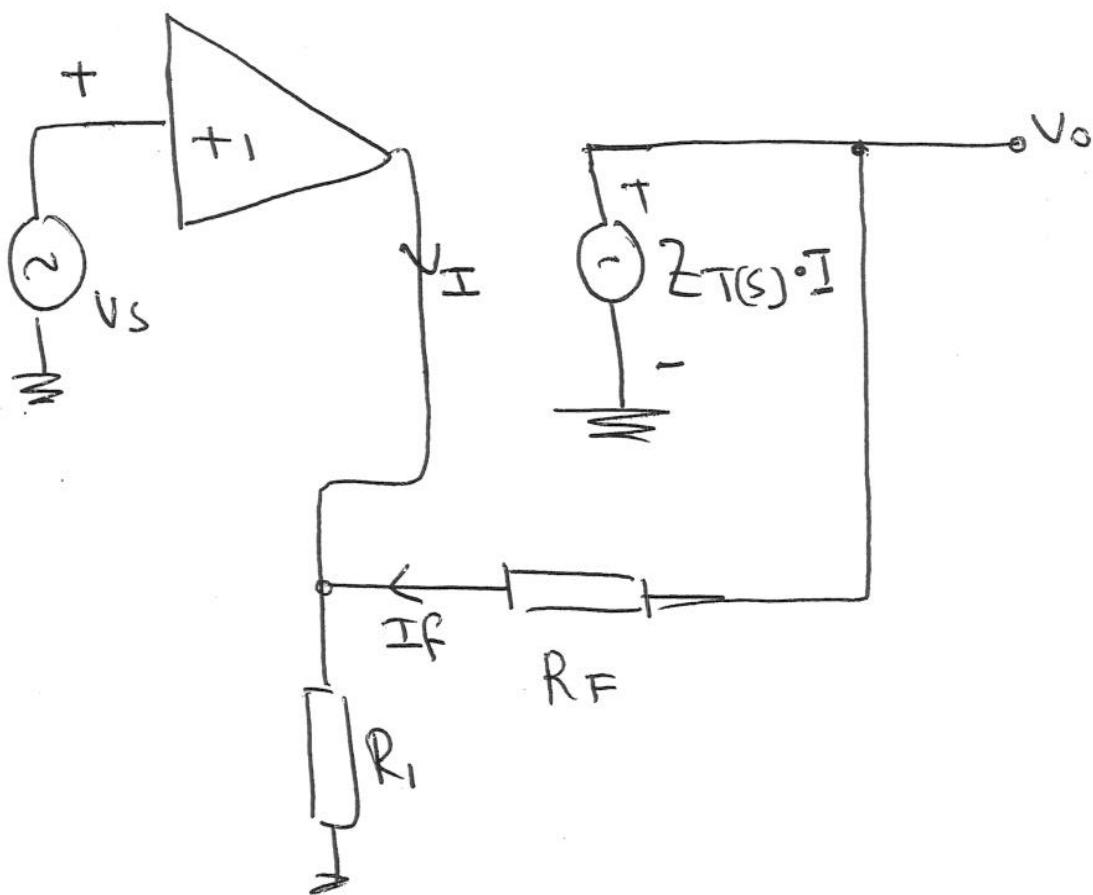
$$\Delta V_{IN} & \underline{2\Delta V}.$$

(15)

Ques 6 cont

Macromodel of Current-feedback op-amp.

c).



$$Z_T(s) = Z_{T0} / (1 + j\omega / \omega_0) \Rightarrow \omega_0 \text{ dominant pole}$$

From model

$$I_F = (V_O - V_S) / R_F$$

$$I_I = V_S / R_I$$

$$V_O = Z_T(s) I = Z_T(s) (I_I - I_F)$$

From above

$$(V_O / V_S) = (1 + R_F / R_I) \left[\frac{Z_{T0}}{R_F + Z_{T0}} \right]$$

Ques cont

(21)

Substitute $Z(T)$ s, and assume $Z_{T0} \gg R_F$

$$\left(\frac{V_o}{V_s}\right)_{\omega} = \left(1 + \frac{R_F}{R_1}\right) \left[\frac{\frac{Z_{T0}}{Z_{T0} + R_F}}{(1 + jf/f_p) \frac{Z_{T0} + R_F}{R_F}} \right]$$

Assume $Z_{T0} \gg R_F$

$$\left(\frac{V_o}{V_s}\right)_{\omega} = \left(1 + \frac{R_F}{R_1}\right) \frac{1}{\left(1 + jf/\frac{G \cdot B}{R_F}\right)}$$

where $G \cdot B = f_p Z_{T0}$

f_p closed = $\underline{\underline{\frac{G \cdot B}{R_F}}} \Rightarrow$ determined by R_F

Can be determined by R ,

$$A_C = \left(1 + \frac{R_F}{R_1}\right)$$

$$\underline{\underline{}}$$

(7)

(T)